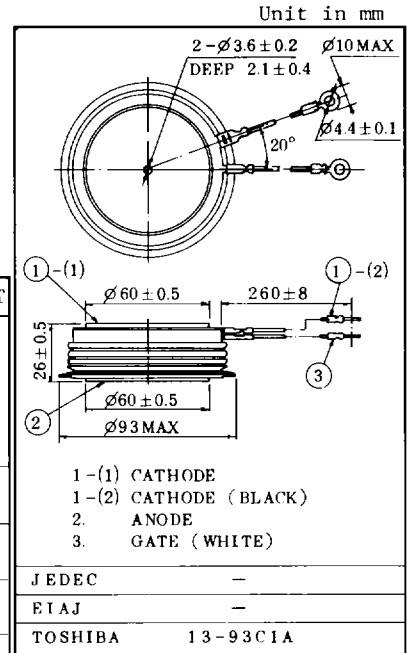


CHOPPER, INVERTER APPLICATION

- . Repetitive Peak Off-State Voltage : $V_{DRM}=1300, 1600, 1800, 2500V$
- . R.M.S On-State Current : $I_T(RMS)=700A$
- . Peak Turn-Off Current : $I_{TGQM}=2000A$
- . Critical Rate of Rise of On-State Current : $di/dt=300A/\mu s$
- . Critical Rate of Rise of Off-State Voltage : $dv/dt=500V/\mu s$

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	SG2000R22	V_{DRM}	1300	V
	SG2000U22		1600	
	SG2000W22		1800	
	SG2000EX22		2500	
Repetitive Peak Reverse Voltage		V_{RRM}	15	V
Peak Turn-Off Current (Note 1)		I_{TGQM}	2000	A
R.M.S On-State Current (Note 2)		$I_T(RMS)$	700	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	14000(50Hz)	A
			15400(60Hz)	
Critical Rate of Rise of On-State Current (Note 3)		di/dt	300	A/ μs
Peak Forward Gate Current (Note 4)		I_{FGM}	70	A
Average Forward Gate Power Dissipation		$P_{G(AV)}$	14	W
R.M.S Reverse Gate Current		$I_{RG(RMS)}$	60	A
Peak Reverse Gate Power Dissipation (Note 5)		P_{RGM}	15	kW
Peak Reverse Gate Voltage		V_{RGM}	15	V
Storage Temperature Range		T_{stg}	-40~125	$^{\circ}C$
Operating Junction Temperature Range		T_j	-40~125	$^{\circ}C$
Mounting Force		-	2000 \pm 200	kg



Weight : 800g

Note 1 : $V_D=1/2$ Rated, $C_S=4\mu F$, $R_S=5\Omega$, $di_{RG}/dt=40A/\mu s$, $I_{RG} \neq 400A$
 $T_j=120^{\circ}C$, ($V_{DSP} \leq 600V$)

Note 2 : Half Sine Waveform

Note 3 : $V_D=1/2$ Rated, $I_{TM}=2000A$, $I_G=30A$, $t_r=1\mu s$, $f=50Hz$, $T_j=125^{\circ}C$

Note 4 : Pulse Width : Max. 30 μs , Duty : Max. 20%

Note 5 : Pulse Width : Max. 50 μs , Duty : Max. 2%

SG2000(R,U,W,EX)22

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current	I_{DRM}	$V_{DRM}=\text{Rated}$, $R_{GK}=10\Omega$ $T_j=125^\circ\text{C}$	-	-	50	mA	
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM}=\text{Rated}$, $T_j=125^\circ\text{C}$	-	-	100	mA	
Repetitive Peak Reverse Gate Current	I_{RGM}	$V_{RGM}=\text{Rated}$, $T_j=125^\circ\text{C}$	-	-	100	mA	
Peak On-State Voltage	V_{TM}	$I_{TM}=2000\text{A}$, $T_c=25^\circ\text{C}$	-	-	2.8	V	
Gate Trigger Voltage	V_{GT}	$V_D=24\text{V}$ $R_L=0.1\Omega$	$T_c=-40^\circ\text{C}$	-	-	1.5	V
			$T_c=25^\circ\text{C}$	-	-	1.2	
Gate Trigger Current	I_{GT}	$R_L=0.1\Omega$	$T_c=-40^\circ\text{C}$	-	-	6.0	A
			$T_c=25^\circ\text{C}$	-	-	2.5	
Gate Non-Trigger Voltage	V_{GD}	$V_D=1/2 \text{ Rated}$, $T_c=125^\circ\text{C}$	0.3	-	-	V	
Gate Non-Trigger Current	I_{GD}		10	-	-	mA	
Delay Time	t_d	$V_D=1/2 \text{ Rated}$ $di/dt=300\text{A}/\mu\text{s}$, $I_{TM}=2000\text{A}$	-	-	4.0	μs	
Turn-On Time	t_{gt}	$I_G=30\text{A}$, $t_r=1\mu\text{s}$, $T_c=25^\circ\text{C}$	-	-	15	μs	
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM}=2/3 \text{ Rated}$ $T_j=125^\circ\text{C}$, $V_{GK}=-4\text{V}$ Exponential Rise	500	-	-	$\text{V}/\mu\text{s}$	
Holding Current	I_H	$T_c=25^\circ\text{C}$, $R_L=0.1\Omega$	-	40	-	A	
Storage Time	t_s	$I_T=2000\text{A}$, $V_D=1/2 \text{ Rated}$	-	-	20	μs	
Gate Turn-Off Time	t_{gq}	$V_{DM}=2/3 \text{ Rated}$, $C_S=4\mu\text{F}$	-	-	23	μs	
Tail Time	t_{tail}	$di_{RG}/dt=40\text{A}/\mu\text{s}$	-	-	60	μs	
Turn-Off Gate Current	I_{RG}	$T_c=120^\circ\text{C}$	-	400	460	A	
Thermal Resistance	$R_{th(j-f)}$	Junction to Fin	-	-	0.025	$^\circ\text{C}/\text{W}$	

